



WANSEMI
万芯半导体

WP30100AFA

Enhancement Mode N-Channel Power MOSFET

TO-220F/NMOS/30V/ ± 20 V/1.8V/100A/3.1m Ω

Rev0.5

Enhancement Mode N-Channel Power MOSFET

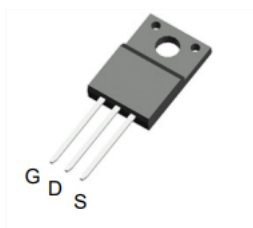
1.Features

- ◆ Fast Switching
- ◆ Improved dv/dt Capability

2.Applications

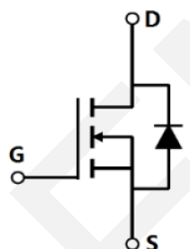
- ◆ Load Switch
- ◆ PWM Application
- ◆ Power management

V_{DS}	$R_{DS(on)}$ Typ.	I_D Max.
30V	3.1mΩ @ 10V	100A
	5.7mΩ @ 4.5V	



Pin Description

TO-220F



Schematic Diagram

3.Package Marking and Ordering Information

Part no.	Marking	Package	PCS/Tube	PCS/CTN.
WP30100AFA	WP30100A	TO-220F	50	5,000

4.Absolute Max Ratings at Ta=25°C (Note1)

Parameter	Symbol	Value	Units
Drain to Source Voltage	V_{DS}	30	V
Gate to Source Voltage	V_{GS}	±20	V
Drain Current (DC)	I_D	100	A
Drain Current (Pulse), $PW \leq 300\mu s$	I_{DP}	400	A
Total Dissipation	P_D	78	W
Avalanche Energy, Single Pulsed	E_{AS}	82	mJ
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

5. Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to case	$R_{\theta JC}$	1.6	$^{\circ}\text{C/W}$
Junction to ambient	$R_{\theta JA}$	42	$^{\circ}\text{C/W}$

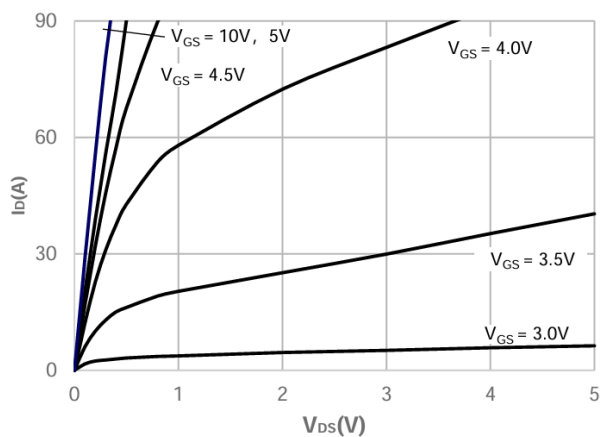
Note 2: When mounted on 1 inch square copper board $t \leq 10\text{sec}$ The value in any given application depends on the user's specific board design.

6. Electrical Characteristics at $T_a=25^{\circ}\text{C}$ (Note 3)

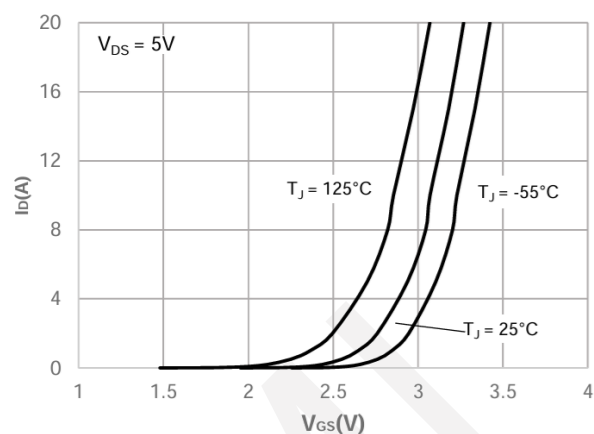
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	30	-	-	V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{V}$, $V_{GS} = 0\text{V}$	-	-	1	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{DS}=250\mu\text{A}$	1.0	1.8	2.5	V
Static Drain to Source On-State Resistance	$R_{DS(on)}$	$I_D = 30\text{A}$, $V_{GS} = 10\text{V}$	-	3.1	4.0	$\text{m}\Omega$
		$I_D = 20\text{A}$, $V_{GS} = 4.5\text{V}$	-	5.7	7.0	$\text{m}\Omega$
Input Capacitance	C_{iss}	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, Frequency=1.0MHz	-	2264	-	pF
Output Capacitance	C_{oss}		-	302	-	pF
Reverse Transfer Capacitance	C_{rss}		-	246	-	pF
Turn-ON Delay Time	$t_{d(on)}$	$V_{GS}=10\text{V}$, $V_{DS} = 15\text{V}$, $I_D = 30\text{A}$, $R_G = 3\Omega$	-	9	-	ns
Rise Time	t_r		-	19	-	ns
Turn-OFF Delay Time	$t_{d(off)}$		-	37	-	ns
Fall Time	t_f		-	13	-	ns
Total Gate Charge	Q_g	$V_{DS} = 15\text{V}$, $V_{GS} = 0$ to 10V , $I_D = 30\text{A}$	-	44	-	nC
	Q_{gs}		-	9	-	nC
	Q_{gd}		-	11	-	nC
Diode Forward Voltage	V_{FSD}	$I_S = 30\text{A}$, $V_{GS} = 0$	0.5	-	1.2	V

Note 3: Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

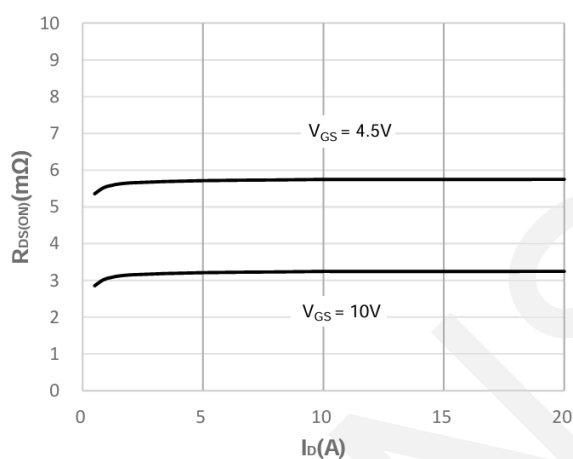
7. Typical electrical and thermal characteristics



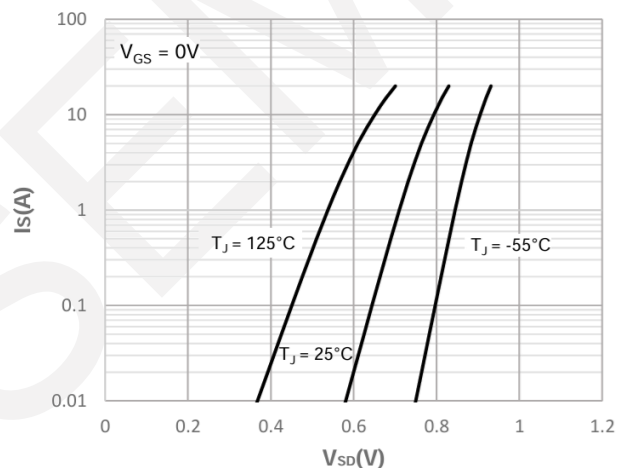
On-Region Characteristics



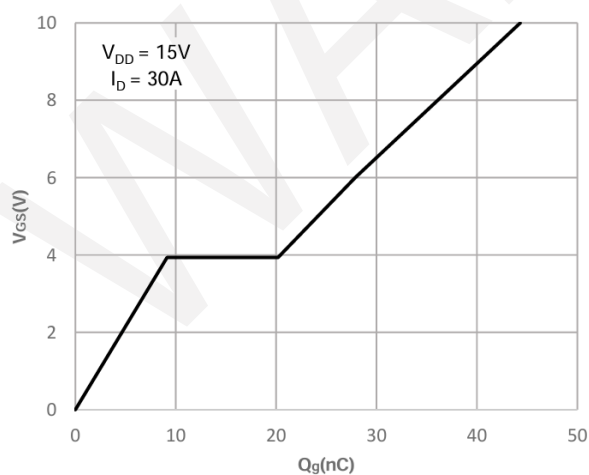
Transfer Characteristics



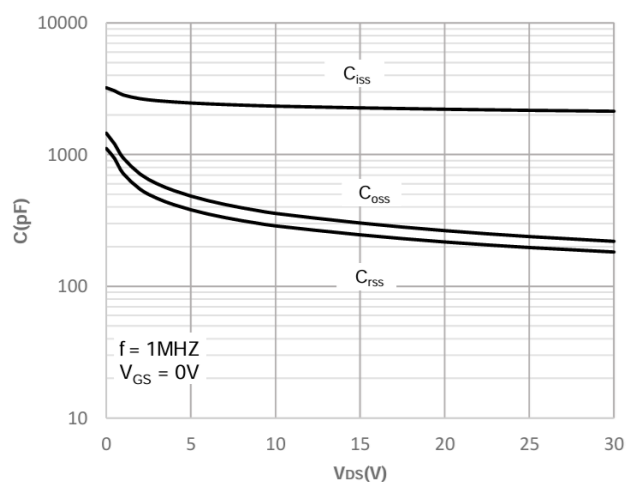
**On-Resistance vs. Drain Current
and Gate Voltage**



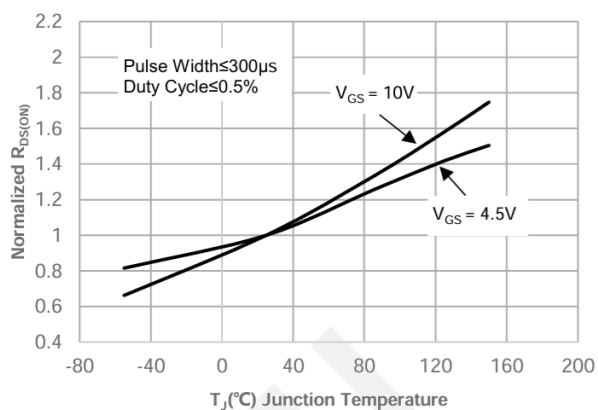
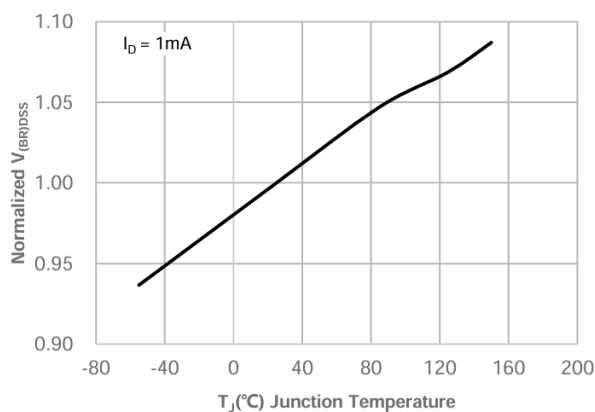
Body Diode Characteristics



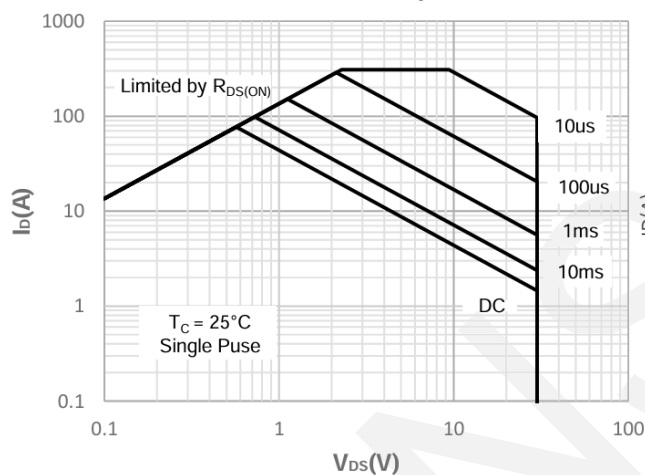
Gate Charge Characteristics



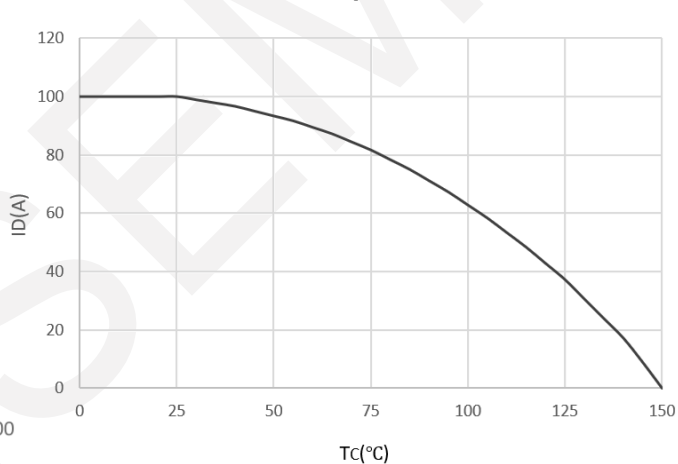
Capacitance Characteristics



Normalized Breakdown voltage vs. Junction Temperature

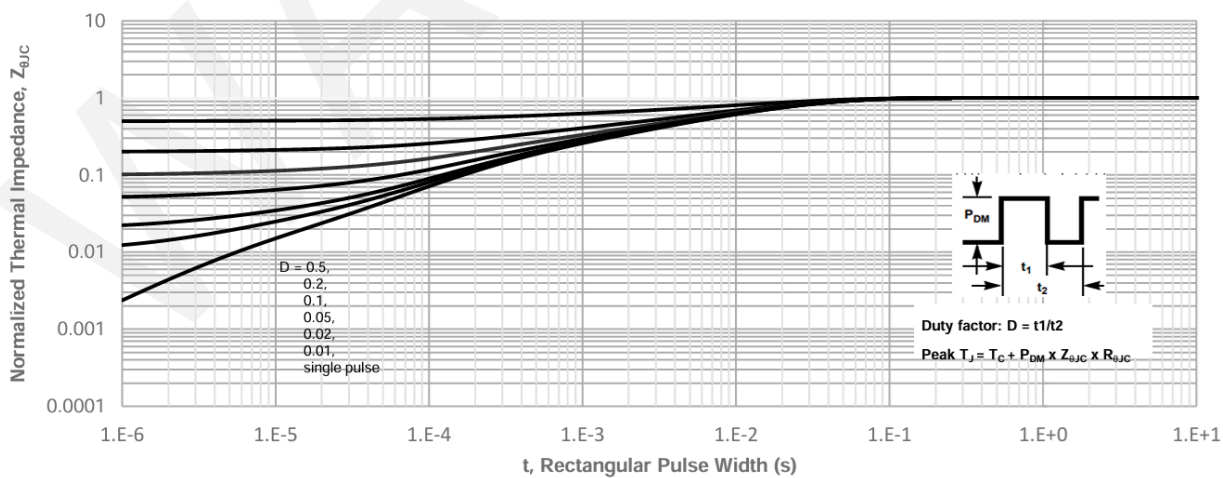


Normalized on Resistance vs. Junction Temperature



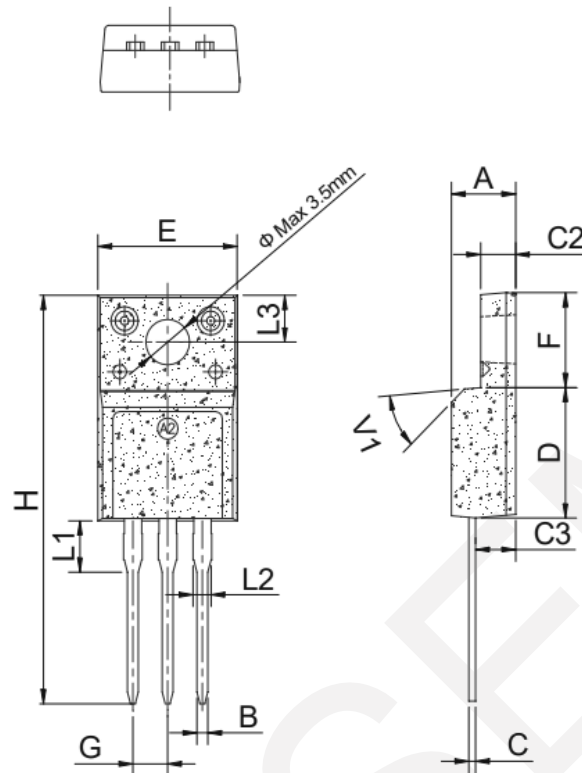
Maximum Forward Biased Safe Operating Area

Current De-rating



Normalized Maximum Transient Thermal Impedance

8.Package Dimensions



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

9. Important Notice

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